

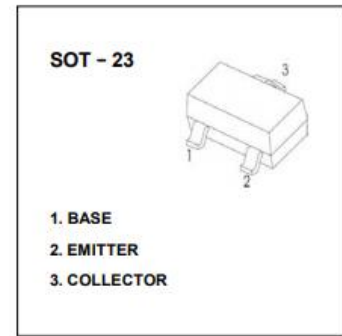


SOT-23 Plastic-Encapsulate Transistors

SS8050 TRANSISTOR (NPN)

FEATURES

Complimentary to SS8550 0.7A



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

Symbol (符号)	Parameter (参数名称)	Value (额定值)	Units (单位)
VCBO	Collector-Base Voltage (集电极-基极电压)	40	V
VCEO	Collector-Emitter Voltage (集电极-发射极电压)	25	V
VEBO	Emitter-Base Voltage (发射极-基极电压)	5	V
IC	Collector Current -Continuous (集电极电流)	0.7	A
PC	Collector Power Dissipation (耗散功率)	0.3	W
Tj	Junction Temperature (结温)	150	°C
Tstg	Storage Temperature (储存温度)	-55-150	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

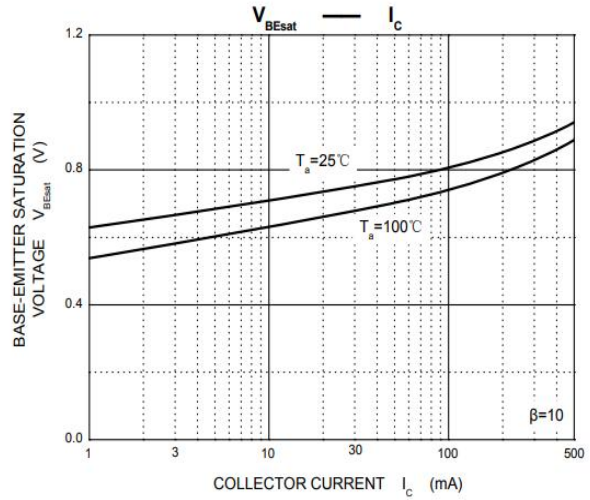
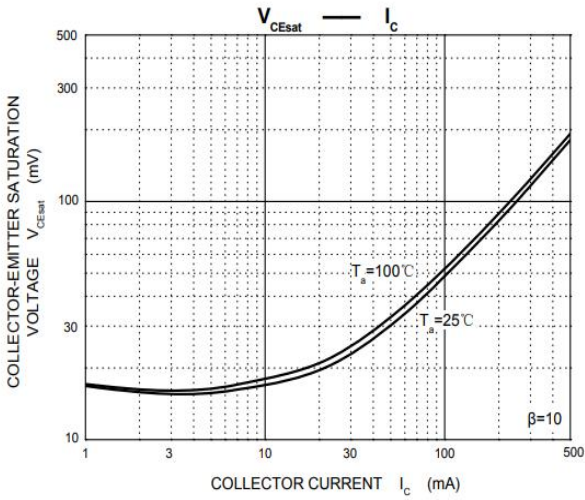
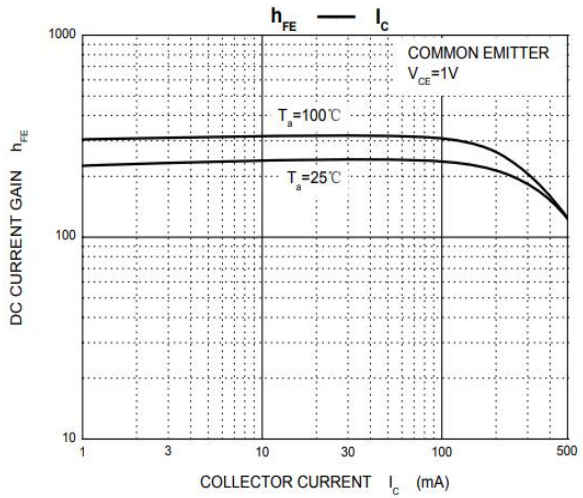
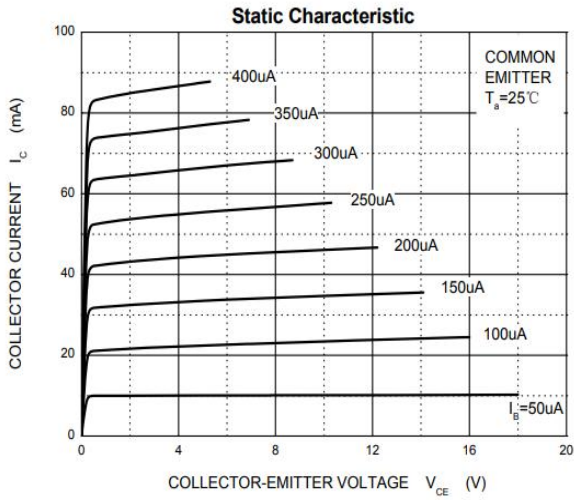
Parameter (参数名称)	Symbol (符号)	Test conditions (测试条件)	MIN (最小值)	TYP (典型值)	MAX (最大值)	UNIT (单位)
Collector-base breakdown voltage 集电极-基极击穿电压	V(BR)CBO	IC= 100μA, IE=0	40			V
Collector-emitter breakdown voltage 集电极-发射极击穿电压	V(BR)CEO	IC= 1mA, IB=0	25			V
Emitter-base breakdown voltage 发射极-基极击穿电压	V(BR)EBO	IE=100μA, IC=0	5			V
Collector cut-off current 集电极-基极截止电流	ICBO	VCB=30 V, IE=0			1	μA
Collector cut-off current 集电极-发射极截止电流	ICEO	VCE=25V, IB=0			10	μA
Emitter cut-off current 发射极-基极截止电流	IEBO	VEB=5V, IC=0			1	μA
DC current gain 直流电流增益	hFE	VCE=1V, IC= 50mA	80		400	
Collector-emitter saturation voltage 集电极-发射极饱和和压降	VCE(sat)	IC=500mA, IB=50mA			0.5	V
Base-emitter saturation voltage 发射极-基极饱和和压降	VBE(sat)	IC=500mA, IB=50mA			1.2	V

CLASSIFICATION OF hFE

Range	80-100	100-200	200-400

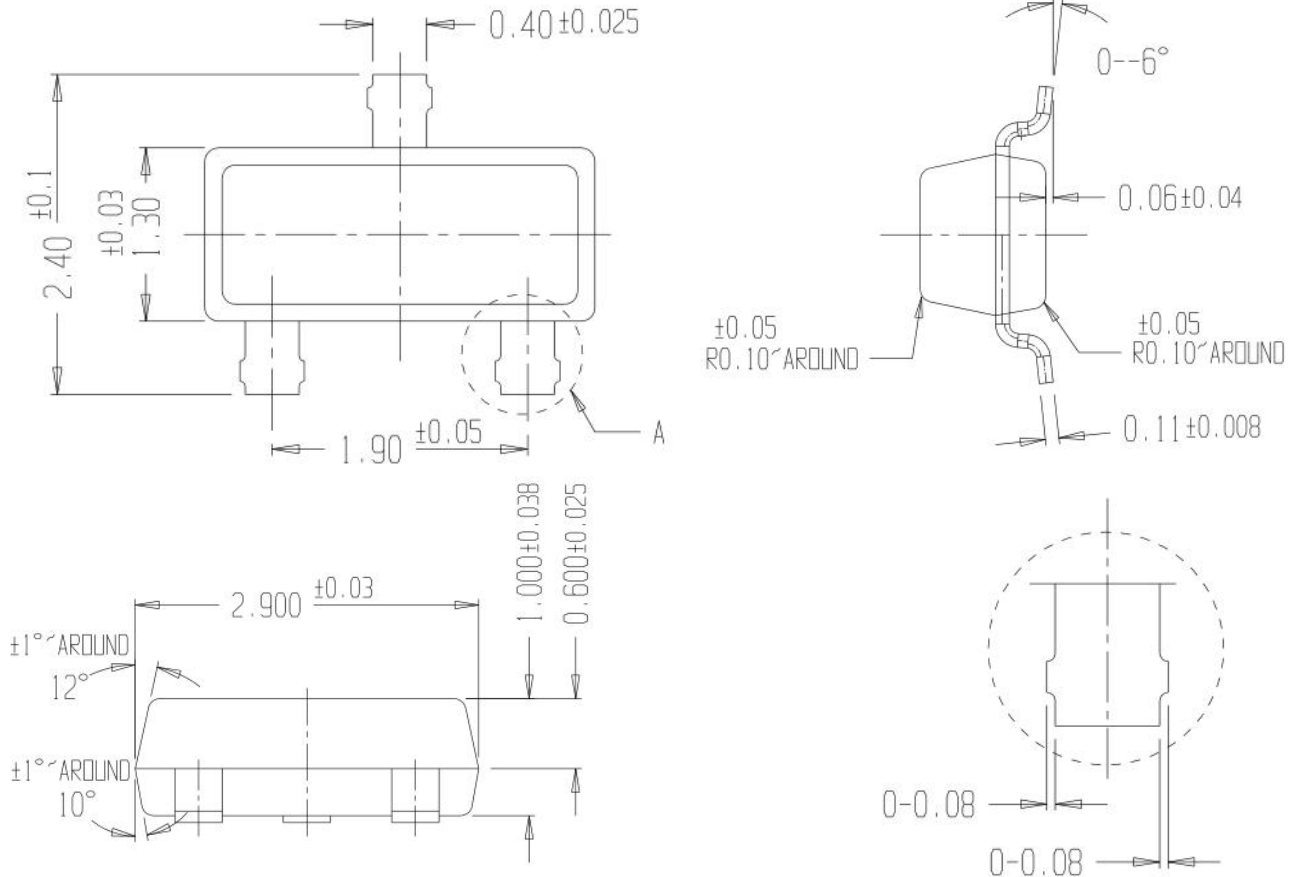


Typical Characteristics





SOT-23 Package information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.962	1.038	0.038	0.040
A1	0.575	0.625	0.023	0.025
b	0.40	0.60	0.016	0.024
c	0.08	0.15	0.003	0.06
D	2.87	2.93	0.113	0.115
E	1.27	1.33	0.05	0.052
E1	2.3	2.5	0.090	0.098
e 1	1.85	1.95	0.073	0.077
L	0.31	0.44	0.012	0.017
L1	0.50	0.60	0.020	0.024
e	0.02	0.1	0.000	0.004